



2812

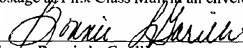
Docket No. 740819-442

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Akihiko ISHIBASHI et al.) Examiner: Savitri Mulpuri
Serial No. 09/692,211)
Filed: October 20, 2000) Group Art Unit: 2812
For: METHOD OF FABRICATING NITRIDE SEMI-) Confirmation No.: 6705
CONDUCTOR DEVICE)

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231, on April 15, 2003.


Name: Bonnie L. Garfill

REQUEST FOR ACKNOWLEDGMENT OF
INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, D.C. 20231

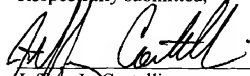
Sir:

An Information Disclosure Statement with Form PTO-1449 was filed in the above-identified patent application on September 19, 2002. Applicants have received back from the Examiner a partially considered copy of the Form PTO-1449 initialed to acknowledge the fact that the Examiner has considered the cited disclosed information.

The Examiner is requested to initial and return to the undersigned a copy of the subject Form PTO-1449.

Should there be any questions concerning this communication, please telephone the undersigned at the number set forth below.

Respectfully submitted,


Jeffrey L. Costellia
Registration No. 35,483

Nixon Peabody LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 770-9300

RECEIVED
APR 23 2003
PC 2800 MAIL ROOM

Form PTO-1449 Rev. 8-83 <div style="border: 1px solid black; border-radius: 50%; padding: 5px; display: inline-block; transform: rotate(-45deg);"> SEP 23 2002 PATENT & TRADEMARK OFFICE </div>	U.S. Department of Commerce Patent and Trademark Office	Atty Docket 740819-442 Serial No. 09/692,211 Applicants: Akihiko ISHIBASHI et al. Filing Date: October 20, 2000 Group Art Unit: 2842	APR 21 2003 PATENT & TRADEMARK OFFICE			
INFORMATION DISCLOSURE STATEMENT						
U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,787,104	07/28/1998	Kamiyama et al.			
FOREIGN PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
	0 887 436	12/30/1998	EP			Full Eng
	07-235505	09/05/1995	JP			Part Eng
	08-255932	10/01/1996	JP			X
	08-316141	11/29/1996	JP			Part Eng
	09-213998	08/15/1997	JP			Part Eng
	10-182282	07/07/1998	JP			Part Eng
	11-074203	03/16/1999	JP			Part Eng
	2702889	10/03/1997	JP			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
Examiner Initial						
	Miyake et al., "Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy", pp. L1000-L1002, September 15, 1999, Jpn. J. Appl. Phys., Vol 38, Part 2, No. 9A/B					
	Nakamura et al., "AlN and AlGaIn Growth Using Low-Pressure Metalorganic Chemical Vapor Deposition", pp. 280-285, 1998, Journal of Crystal Growth 195					
	Mihopoulos, et al., "A Reaction-Transport Model for AlGaIn MOVPE Growth", pp. 733-739, 1998, Journal of Crystal Growth 195					
	Lee et al., "Characteristics of In Ga N/GaN Grown by LPMOVPE with the Variation of Growth Temperature", pp. 6-10, 1997, Journal of Crystal Growth 182					
Examiner			Date Considered			

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.